

ABSTRACT

A method for programming a read-only memory cell including a transistor whose source and drain, which have a second type of doping, are formed in a semiconductor substrate with a first type of doping, includes a step of carrying out a contradoping in a region of the source, the region being
5 adjacent to the conduction channel 4, to make it a region with the first type of doping so as to prevent a transistor effect from occurring.